

D3SBA10 ~ D3SBA100

SILICON BRIDGE RECTIFIER

PRV : 100 ~ 1000 Volts

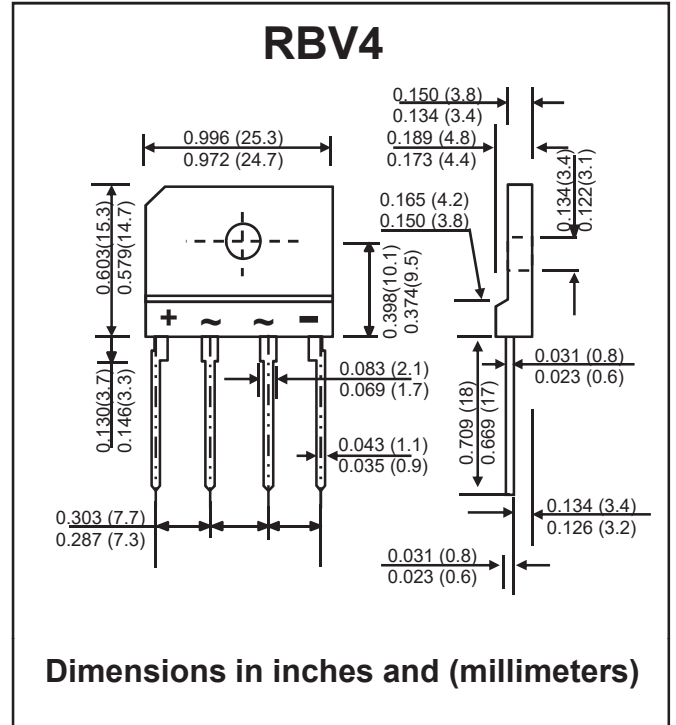
Io : 4.0 Amperes

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Ideal for printed circuit board
- * Very good heat dissipation
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 4.28 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	D3SBA10	D3SBA20	D3SBA40	D3SBA60	D3SBA80	D3SBA100	UNIT
Maximum Reverse Voltage	V_{RM}	100	200	400	600	800	1000	V
Maximum Average Forward Current (60Hz Sine wave, R-load)	$I_{F(AV)}$	4 (With heatsink, $T_c = 110^{\circ}C$) 2.3 (Without heatsink, $T_a = 25^{\circ}C$)						A
Maximum Peak Forward Surge Current (60 Hz, Half-cycle, Sinwave, Single Shot)	I_{FSM}	135						A
Current Squared Time at $1ms \leq t < 8.3 ms, T_j=25^{\circ}C$	I^2t	75						A ² S
Maximum Forward Voltage per Diode at $I_F = 2.0 A$.	V_F	1.0						V
Maximum DC Reverse Current, $V_R=V_{RM}$ (Pulse measurement, Rating of per diode)	I_R	5						μA
Maximum Thermal Resistance, Junction to case	$R_{\theta JC}$	5.0 (With heatsink)						$^{\circ}C/W$
Maximum Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	30 (Without heatsink)						$^{\circ}C/W$
Operating Junction Temperature Range	T_J	- 55 to + 150						$^{\circ}C$
Storage Temperature Range	T_{STG}	- 55 to + 150						$^{\circ}C$

RATING AND CHARACTERISTIC CURVES (D3SBA10 ~ D3SBA100)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

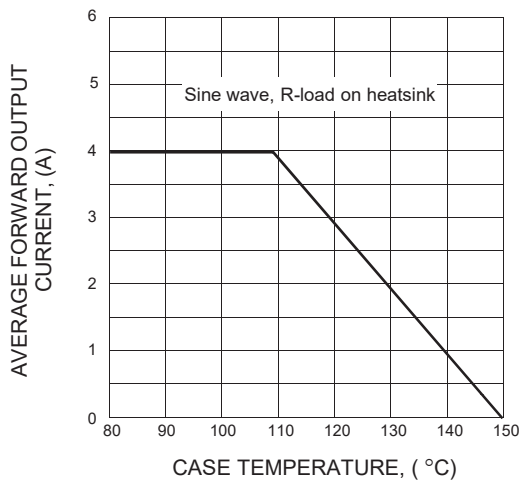


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

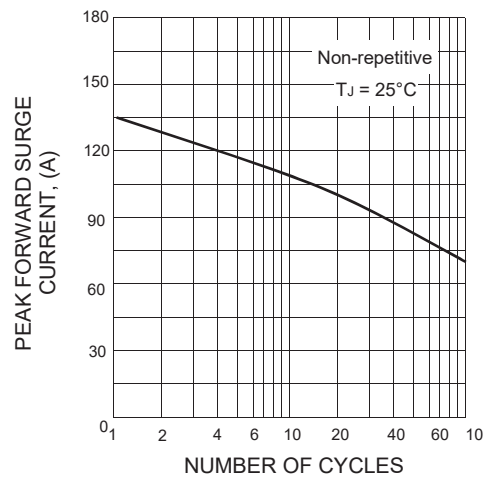


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

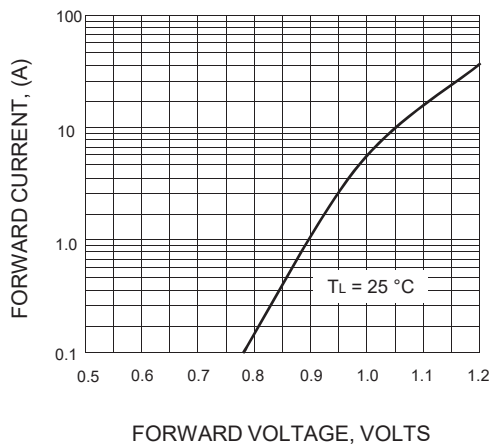


FIG.4 - POWER DISSIPATION

